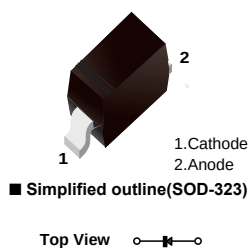


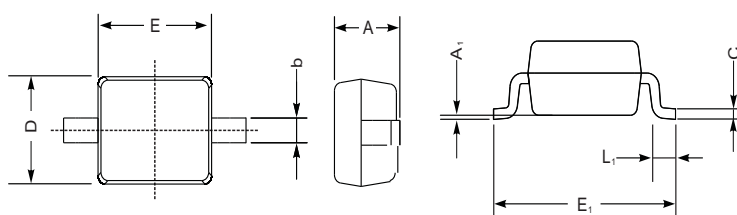


FEATURES

- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives



SOD323



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—
mil	max	43	5.9	55	70	108	16	16	8
	min	32	3.1	47	63	100	9.8	7.9	—

Absolute Maximum Ratings at 25 °C

Parameter	Symbols	BAS20H	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Maximum RMS voltage	V_{RMS}	150	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-reptitive Peak Forward Surge Current at 1s at 1ms at 1 us	I_{FSM}	1 3 9	A
Total Power Dissipation	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

BAS20H

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbols	BAS20H	Units
Reverse Breakdown Voltage at $I_R=100\mu\text{A}$	$V_{(BR)R}$	200	V
Maximum Forward Voltage at 100 m A at 200 m A	V_F	1.00 1.25	V
Maximum DC Reverse Current $T_a = 25\text{ }^{\circ}\text{C}$ at Rated DC Blocking Voltage $T_a = 150\text{ }^{\circ}\text{C}$	I_R	0.1 100	μA
Typical Junction Capacitance at $V_R=4\text{V}$, $f=1\text{MHz}$	C_j	5	pF
Maximum Reverse Recovery Time	t_{rr}	50	ns

RATING AND CHARACTERISTIC CURVES (BAS20H)

Fig.1 Forward Current Derating Curve

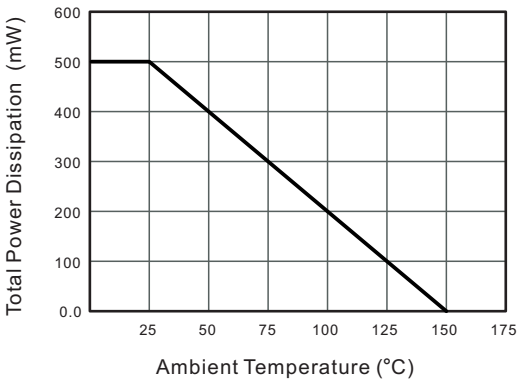


Fig.2 Typical Reverse Characteristics

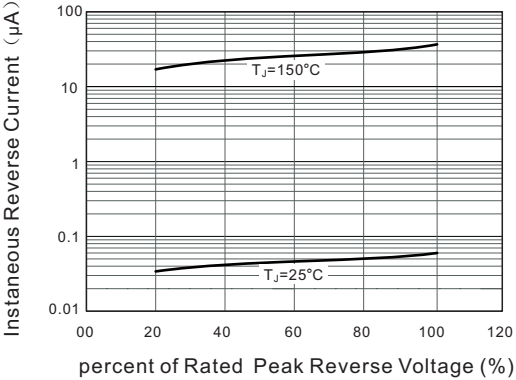


Fig.3 Typical Instaneous Forward Characteristics

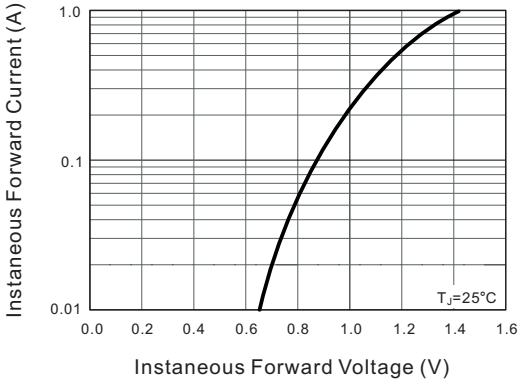


Fig.4 Typical Junction Capacitance

